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Kind regards,

Team Nexperia

### **DISCRETE SEMICONDUCTORS**

# DATA SHEET

**PEMH7**; **PUMH7** NPN/NPN resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

Product data sheet Supersedes data of 2001 Oct 22 2003 Oct 02



## NPN/NPN resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

PEMH7; PUMH7

TYP. MAX. UNIT

#### **FEATURES**

- Built-in bias resistors
- · Simplified circuit design
- · Reduction of component count
- · Reduced pick and place costs.

#### **APPLICATIONS**

- · Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- . Control of IC inputs.

V <sub>CEO</sub>	collector-emitter voltage	-	50	V
lo	output current (DC)	_	100	mA
TR1	NPN	_	_	_
TR2	NPN	=	_	_
R1	bias resistor	4.7	_	kΩ
R2	bias resistor	open	_	_

**PARAMETER** 

**QUICK REFERENCE DATA** 

SYMBOL

#### **DESCRIPTION**

NPN/NPN resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

#### **PRODUCT OVERVIEW**

TYPE NUMBER	PACKAGE		MARKING CODE <sup>(1)</sup>	NPN/PNP	PNP/PNP
TIPE NOMBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	COMPLEMENT
PEMH7	SOT666	_	H3	PEMD6	PEMB3
PUMH7	SOT363	SC-88	H*7	PUMD6	PUMB3

#### Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.

#### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING
TIPE NOMBER	SIMPLIFIED OUTLINE AND STIMBOL	PIN	DESCRIPTION
PEMH7 PUMH7	6 5 4 Top view MAM453	1 2 3 4 5 6	emitter TR1 base TR1 collector TR2 emitter TR2 base TR2 collector TR1

## NPN/NPN resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

PEMH7; PUMH7

#### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE						
ITPE NUMBER	NAME	DESCRIPTION	VERSION					
PEMH7	_	Plastic surface mounted package; 6 leads	SOT666					
PUMH7	1	Plastic surface mounted package; 6 leads	SOT363					

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transist	tor		•	•	- 1
V <sub>CBO</sub>	collector-base voltage	open emitter	_	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V
Io	output current (DC)		-	100	mA
I <sub>CM</sub>	peak collector current		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363	note 1	_	200	mW
	SOT666	notes 1 and 2	_	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C
Per device	•				•
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363	note 1	_	300	mW
ı	SOT666	notes 1 and 2	_	300	mW

### Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

# NPN/NPN resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	notes 1 and 2	416	K/W

#### **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT	
Per transis	stor	•	•	•	•	
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0	_	_	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0$	_	_	1	μΑ
		$V_{CE} = 30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0$	_	_	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	200	330	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$	_	_	100	mV
R1	input resistor		3.3	4.7	6.1	kΩ
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0; f = 1 \text{ MHz}$	_	_	2.5	pF

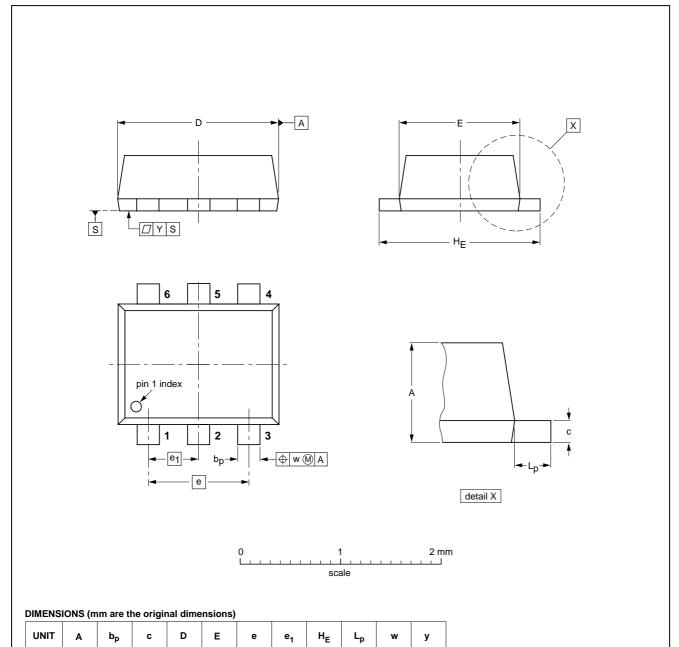
# NPN/NPN resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

PEMH7; PUMH7

#### **PACKAGE OUTLINE**

Plastic surface mounted package; 6 leads

SOT666



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						<del>-01-01-04</del> 01-08-27

0.3

0.1

2003 Oct 02 5

0.6

mm

0.27 0.17

0.18

0.08

1.7

1.3

1.0

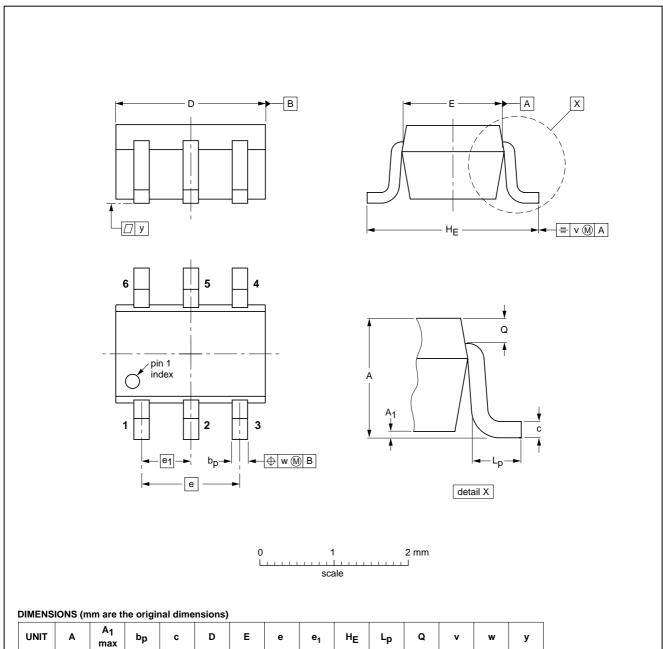
0.5

# NPN/NPN resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

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#### Plastic surface mounted package; 6 leads

**SOT363** 



UNIT	A	A <sub>1</sub> max	bp	С	D	Е	е	e <sub>1</sub>	HE	Lp	Q	v	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC JEDEC EIAJ			PROJECTION	1920E DATE	
SOT363			SC-88			97-02-28

### NPN/NPN resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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#### **Customer notification**

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#### **Contact information**

For additional information please visit: http://www.nxp.com

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Printed in The Netherlands R75/03/pp8 Date of release: 2003 Oct 02 Document order number: 9397 750 11873



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